Docket No.: 51876P422

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re the Application of:

SOON-YONG KWEON

Application No.:

Filed:

For: FERROELECTRIC RANDOM ACCESS

MEMORY CAPACITOR AND METHOD FOR MANUFACTURING THE SAME

Art Group:

Examiner:

## INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure, enclosed is a copy of Information Disclosure Statement by Applicant (form PTO/SB/08), which is being submitted concurrently with the Utility Application. It is respectfully requested that the cited references be considered and that the enclosed copy of PTO/SB/08 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

-l- 51876P422

The submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made in the subject application and is not to be construed as an admission that the information cited in this statement is material to patentability.

Please charge any fees due to Deposit Account 02-2666. A duplicate copy of the Fee Transmittal (PTO/SB/17) is enclosed for this purpose.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAEMAN LLP

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Date: December 08, 2003

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				C mplete if Known	
				Application Number	
				Filing Date	
				First Named Inventor	Soon-Yong Kweon
				Art Unit	
				Examiner Name	
Sheet	1	of	1	Attorney Docket Number	51876P422

NON PATENT LITERATURE DOCUMENTS						
Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²			
		KR Laid-Open No. 2003-23844				
		0.18 µm SBT-Based Embedded FeRAM Operating at a Low Voltage of 1.1V (2003 Symposium on VLSI Technology Digest of Technical Papers)				
		Highly Manufacturable and Reliable 32 Mb FRAM Technology with Novel BC and Capacitor Cleaning Process (2003 Symposium on VLSI Technology Digest of Technical Papers)				

Examiner	Date	
Signature	Considered	

<sup>\*</sup>Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication.

<sup>&</sup>lt;sup>1</sup>Applicant's unique citation designation number. <sup>2</sup>Applicant is to place a check mark here if English language Translation is attached.